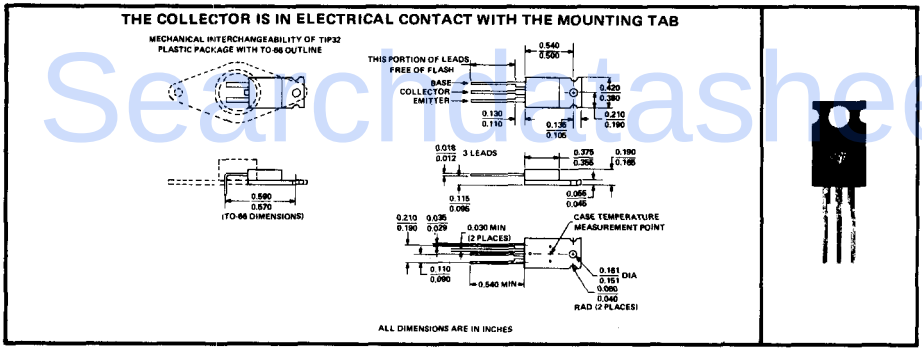
TYPES TIP32, TIP32A, TIP32B, TIP32C
P-N-P SINGLE-DIFFUSED MESA SILICON POWER TRANSISTORS

FOR POWER-AMPLIFIER AND HIGH-SPEED-SWITCHING APPLICATIONS
DESIGNED FOR COMPLEMENTARY USE WITH TIP31, TIP31A, TIP31B, TIP31C

- 40 W at 25°C Case Temperature
- 3 A Rated Collector Current
- Min f_T of 3 MHz at 10 V, 500 mA

mechanical data



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIP32	TIP32A	TIP32B	TIP32C
Collector-Base Voltage	−40 V	−60 V	−80 V	−100 V
Collector-Emitter Voltage (See Note 1)	−40 V	−60 V	−80 V	−100 V
Emitter-Base Voltage	−5 V			
Continuous Collector Current	−3 A			
Peak Collector Current (See Note 2)	−5 A			
Continuous Base Current	−1 A			
Safe Operating Region at (or below) 25°C Case Temperature	See Figure 5			
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	40 W			
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 4)	2 W			
Unclamped Inductive Load Energy (See Note 5)	32 mJ			
Operating Collector Junction Temperature Range	−65°C to 150°C			
Storage Temperature Range	−65°C to 150°C			
Lead Temperature 1/8 Inch from Case for 10 Seconds	260°C			

NOTES: 1. This value applies when the base-emitter diode is open-circuited.
2. This value applies for $t_w \leq 0.3$ ms, duty cycle $\leq 10\%$.
3. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.
4. Derate linearly to 150°C free-air temperature at the rate of 16 mW/°C.
5. This rating is based on the capability of the transistor to operate safely in the circuit of Figure 2. L = 20 mH, $R_{BB2} = 100\ \Omega$, $V_{BB2} = 0$ V, $R_S = 0.1\ \Omega$, $V_{CC} = 10$ V. Energy $\approx I_C^2 L/2$.

electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS	TIP32		TIP32A		TIP32B		TIP32C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = −30 mA, I_B = 0, See Note 6	−40		−60		−80		−100		V
I_{CEO}	Collector Cutoff Current	V_{CE} = −30 V, I_B = 0		−0.3		−0.3					mA
		V_{CE} = −60 V, I_B = 0						−0.3		−0.3	
I_{CES}	Collector Cutoff Current	V_{CE} = −40 V, V_{BE} = 0		−0.2							mA
		V_{CE} = −60 V, V_{BE} = 0				−0.2					
		V_{CE} = −80 V, V_{BE} = 0						−0.2			
		V_{CE} = −100 V, V_{BE} = 0								−0.2	
I_{EBO}	Emitter Cutoff Current	V_{EB} = −5 V, I_C = 0		−1		−1		−1		−1	mA
h_{FE}	Static Forward Current Transfer Ratio	V_{CE} = −4 V, I_C = −1 A, See Notes 6 and 7	25		25		25		25		
		V_{CE} = −4 V, I_C = −3 A, See Notes 6 and 7	10	50	10	50	10	50	10	50	
V_{BE}	Base-Emitter Voltage	V_{CE} = −4 V, I_C = −3 A, See Notes 6 and 7		−1.8		−1.8		−1.8		−1.8	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_B = −375 mA, I_C = −3 A, See Notes 6 and 7		−1.2		−1.2		−1.2		−1.2	V
h_{fe}	Small-Signal Common-Emitter Forward Current Transfer Ratio	V_{CE} = −10 V, I_C = −0.5 A, f = 1 kHz	20		20		20		20		
$\lvert h_{fe} \rvert$	Small-Signal Common-Emitter Forward Current Transfer Ratio	V_{CE} = −10 V, I_C = −0.5 A, f = 1 MHz	3		3		3		3		

NOTES: 6. These parameters must be measured using pulse techniques. t_w = 300 μs, duty cycle ≤ 2%.
7. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

thermal characteristics

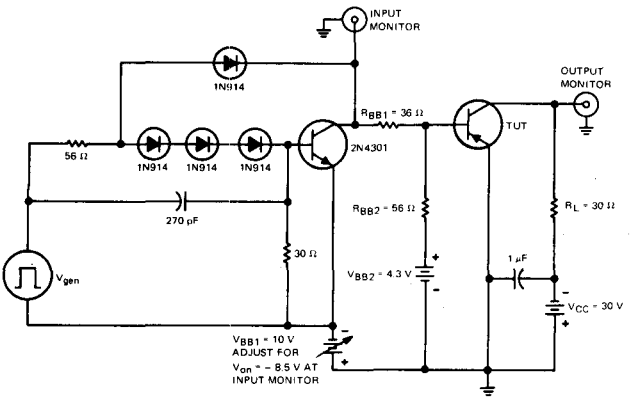
PARAMETER		MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	3.125	°C/W
$R_{\theta JA}$	Junction-to-Free-Air Thermal Resistance	62.5	

switching characteristics at 25°C case temperature

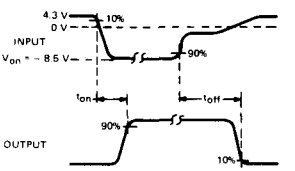
PARAMETER		TEST CONDITIONS†			TYP	UNIT
t_{on}	Turn-On Time	I_C = −1 A,	$I_{B(1)}$ = −100 mA,	$I_{B(2)}$ = 100 mA,	0.3	μs
t_{off}	Turn-Off Time	$V_{BE(off)}$ = 4.3 V,	R_L = 30 Ω,	See Figure 1	1.0	

†Voltages and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

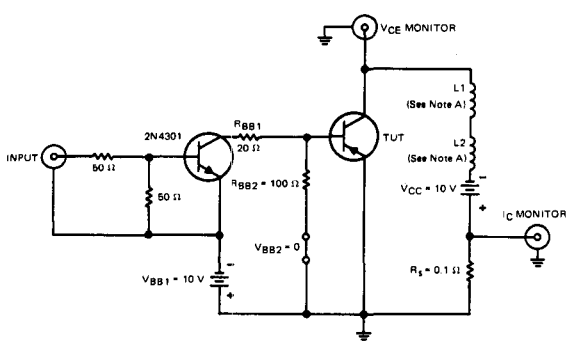


VOLTAGE WAVEFORMS

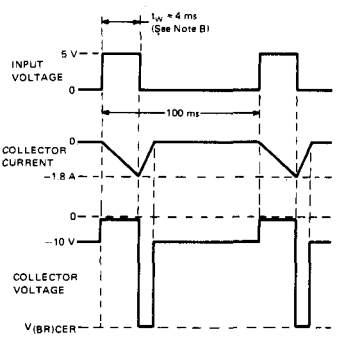
NOTES: A. V_{gen} is a 30-V pulse (from 0 V) into a 50-Ω termination.
B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r \leq 15$ ns, $t_f \leq 15$ ns, $Z_{out} = 50\ \Omega$, $t_w = 20\ \mu s$, duty cycle ≤ 2%.
C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 15$ ns, $R_{in} \geq 10\ M\Omega$, $C_{in} \leq 11.5$ pF.
D. Resistors must be noninductive types.
E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1

INDUCTIVE LOAD SWITCHING



TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS

NOTES: A. L1 and L2 are 10 mH, 0.11 Ω, Chicago Standard Transformer Corporation C-2688, or equivalent.
B. Input pulse width is increased until $I_{CM} = -1.8$ A.

FIGURE 2

TYPICAL CHARACTERISTICS

STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT

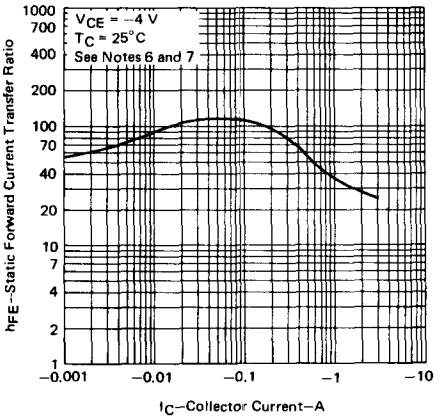


FIGURE 3

NOTES: 6. These parameters must be measured using pulse techniques. t_W = 300 μs, duty cycle ≤ 2%.
7. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

THERMAL INFORMATION

DISSIPATION DERATING CURVE

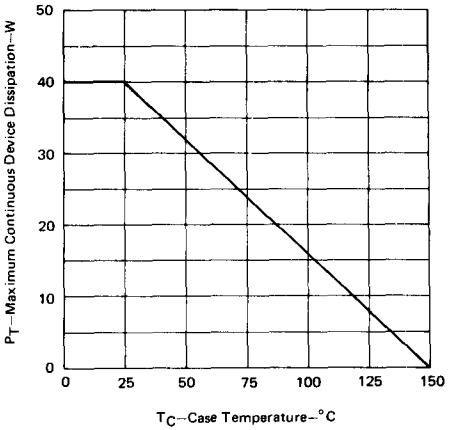


FIGURE 4

MAXIMUM SAFE OPERATING REGION

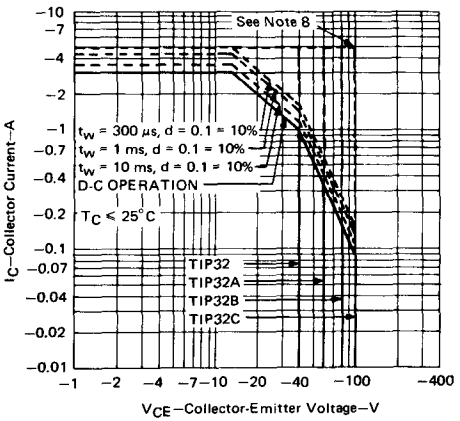


FIGURE 5

NOTE 8: This combination of maximum voltage and current may be achieved only when switching from saturation to cutoff with a clamped inductive load.

SILIZIUM-KOMPLEMENTARE-LEISTUNGSTRANSISTOREN (Allgemeine und NF-Anwendungen)

SILICON COMPLEMENTARY POWER TRANSISTORS (General and Low-frequency Applications)

Typ type NPN	PNP	P_{tot} (@) T_C = 25 °C (100 °C) W	V_{CEO} min	I_{CD} max A	min	h_{FE} (@) max	I_C A
BD 239	BD 240	30	45	2	40		0,2
BD 239 A	BD 240 A	30	60	2	40		0,2
BD 239 B	BD 240 B	30	80	2	40		0,2
BD 239 C	BD 240 C	30	100	2	40		0,2
BD 241	BD 242	40	45	3	25		1
BD 241 A	BD 242 A	40	60	3	25		1
BD 241 B	BD 242 B	40	80	3	25		1
BD 241 C	BD 242 C	40	100	3	25		1
BD 243	BD 244	65	45	6	30		0,3
BD 243 A	BD 244 A	65	60	6	30		0,3
BD 243 B	BD 244 B	65	80	6	30		0,3
BD 243 C	BD 244 C	65	100	6	30		0,3
BD 245	BD 246	80	45	10	40		1
BD 245 A	BD 246 A	80	60	10	40		1
BD 245 B	BD 246 B	80	80	10	40		1
BD 245 C	BD 246 C	80	100	10	40		1
BD 249	BD 250	125	45	25	25		1,5
BD 249 A	BD 250 A	125	60	25	25		1,5
BD 249 B	BD 250 B	125	80	25	25		1,5
BD 249 C	BD 250 C	125	100	25	25		1,5
TIP 29	TIP 30	30	40	1	40	200	0,2
TIP 29 A	TIP 30 A	30	60	1	40	200	0,2
TIP 29 B	TIP 30 B	30	80	1	40	200	0,2
TIP 29 C	TIP 30 C	30	100	1	40	200	0,2
TIP 31	TIP 32	40	40	3	25	100	1
TIP 31 A	TIP 32 A	40	60	3	25	100	1
TIP 31 B	TIP 32 B	40	80	3	25	100	1
TIP 31 C	TIP 32 C	40	100	3	25	100	1
TIP 33	TIP 34	80	40	10	40	125	1
TIP 33 A	TIP 34 A	80	60	10	40	125	1
TIP 33 B	TIP 34 B	80	80	10	40	125	1
TIP 33 C	TIP 34 C	80	100	10	40	125	1
TIP 35	TIP 36	90	40	25	25	100	1,5
TIP 35 A	TIP 36 A	90	60	25	25	100	1,5

f_T min MHz	I_{CES} @ (I_{CEO}) µA	V_{CE} V	Gehäuse package	Anwendungen, Bemerkungen applications, remarks
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	
			TO-66P	Verstärker, Schalter
			TO-66P	amplifier, switch
			TO-66P	
			TO-3P	
			TO-3P	
			TO-3P	
			TO-3P	
			TO-3P	
			TO-3P	
			TO-3P	
			TO-3P	
3	200	40	TO-66P	Verstärker, Schalter, komplementär zu TIP 30 amplifier, switch, complementary to TIP 30
3	200	60	TO-66P	Verstärker, Schalter, komplementär zu TIP 30 A amplifier, switch, complementary to TIP 30 A
3	200	80	TO-66P	Verstärker, Schalter, komplementär zu TIP 30 B amplifier, switch, complementary to TIP 30 B
3	200	100	TO-66P	Verstärker, Schalter, komplementär zu TIP 30 C amplifier, switch, complementary to TIP 30 C
3	300	40	TO-66P	Verstärker, Schalter, komplementär zu TIP 32 amplifier, switch, complementary to TIP 32
3	300	60	TO-3P	Verstärker, Schalter, komplementär zu TIP 32 A amplifier, switch, complementary to TIP 32 A
3	300	80	TO-3P	Verstärker, Schalter, komplementär zu TIP 32 B amplifier, switch, complementary to TIP 32 B
3	300	100	TO-3P	Verstärker, Schalter, komplementär zu TIP 32 C amplifier, switch, complementary to TIP 32 C
3	400	40	TO-3P	Verstärker, Schalter, komplementär zu TIP 34 amplifier, switch, complementary to TIP 34
3	400	60	TO-3P	Verstärker, Schalter, komplementär zu TIP 34 A amplifier, switch, complementary to TIP 34 A
3	400	80	TO-3P	Verstärker, Schalter, komplementär zu TIP 34 B amplifier, switch, complementary to TIP 34 B
3	400	100	TO-3P	Verstärker, Schalter, komplementär zu TIP 34 C amplifier, switch, complementary to TIP 34 C
3	700	40	TO-3P	Verstärker, Schalter, komplementär zu TIP 36 amplifier, switch, complementary to TIP 36
3	700	60	TO-3P	Verstärker, Schalter, komplementär zu TIP 36 A amplifier, switch, complementary to TIP 36 A